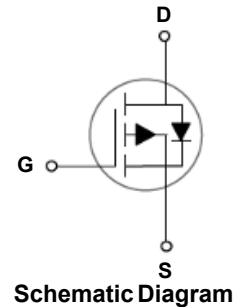
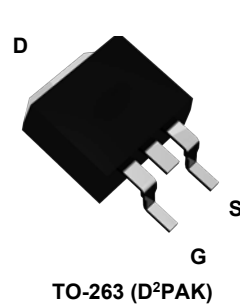


Main Product Characteristics

BV_{DSS}	-60V
$R_{DS(ON)}$	4.6m Ω (Max.)
I_D	-140A



Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The GSFT06130 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous (T _C =25°C)	I_D	-140	A
Drain Current-Continuous (T _C =100°C)		-88	
Drain Current-Pulsed ¹	I_{DM}	-560	A
Single Pulse Avalanche Energy ²	E_{AS}	720	mJ
Single Pulse Avalanche Current ²	I_{AS}	-120	A
Power Dissipation (T _C =25°C)	P_D	183	W
Power Dissipation-Derate above 25°C		1.47	
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.68	°C/W
Operating Junction Temperature Range	T_J	-55 To +150	°C
Storage Temperature Range	T_{STG}	-55 To +150	°C

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
On / Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-60	-	-	V
BV_{DSS} Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	Reference to 25°C , $I_D=1mA$	-	0.036	-	$V/^{\circ}\text{C}$
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=-60V, V_{GS}=0V,$ $T_J=25^{\circ}\text{C}$	-	-	-1	μA
		$V_{DS}=-48V, V_{GS}=0V,$ $T_J=125^{\circ}\text{C}$	-	-	-10	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-50A$	-	3.8	4.6	m Ω
		$V_{GS}=-4.5V, I_D=-25A$	-	5	6	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.2	-1.6	-2.5	V
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}$		-	-6.3	-	mV/ $^{\circ}\text{C}$
Forward Transconductance	g_{fs}	$V_{DS}=-10V, I_D=-3A$	-	18	-	S
Dynamic and Switching Characteristics						
Total Gate Charge ^{3,4}	Q_g	$V_{DS}=-48V, I_D=-5A,$ $V_{GS}=-10V$	-	280	420	nC
Gate-Source Charge ^{3,4}	Q_{gs}		-	30	50	
Gate-Drain Charge ^{3,4}	Q_{gd}		-	60	90	
Turn-On Delay Time ^{3,4}	$t_{d(on)}$	$V_{DD}=-48V, R_G=6\Omega,$ $V_{GS}=-10V, I_D=-1A$	-	87.5	131	nS
Rise Time ^{3,4}	t_r		-	256	380	
Turn-Off Delay Time ^{3,4}	$t_{d(off)}$		-	503	750	
Fall Time ^{3,4}	t_f		-	245	368	
Input Capacitance	C_{iss}	$V_{DS}=-25V, V_{GS}=0V,$ $F=1MHz$	-	16000	24000	pF
Output Capacitance	C_{oss}		-	920	1440	
Reverse Transfer Capacitance	C_{rss}		-	760	1150	
Drain-Source Diode Characteristics and Maximum Ratings						
Continuous Source Current	I_S	$V_G=V_D=0V,$ Force Current	-	-	-140	A
Pulsed Source Current	I_{SM}		-	-	-280	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=-1A,$ $T_J=25^{\circ}\text{C}$	-	-	1	V
Reverse Recovery Time ³	t_{rr}	$V_R=-50V, I_S=-10A,$ $di/dt=100A/\mu s,$ $T_J=25^{\circ}\text{C}$	-	75	-	nS
Reverse Recovery Charge ³	Q_{rr}		-	110	-	nC

Note:

1. Repetitive rating: Pulsed width limited by maximum junction temperature.
2. $V_{DD}=-25V, V_{GS}=-10V, L=0.1mH, I_{AS}=-120A, R_G=25\Omega,$ starting $T_J=25^{\circ}\text{C}$.
3. Pulse test: pulse width $\leq 300\mu s,$ duty cycle $\leq 2\%$.
4. Essentially independent of operating temperature.

Typical Electrical and Thermal Characteristic Curves

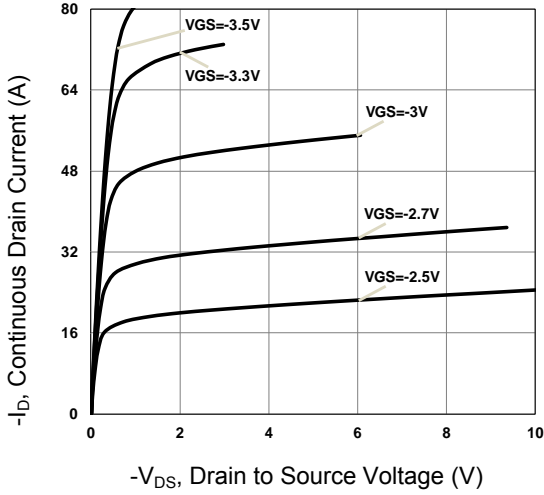


Figure 1. Typical Output Characteristics

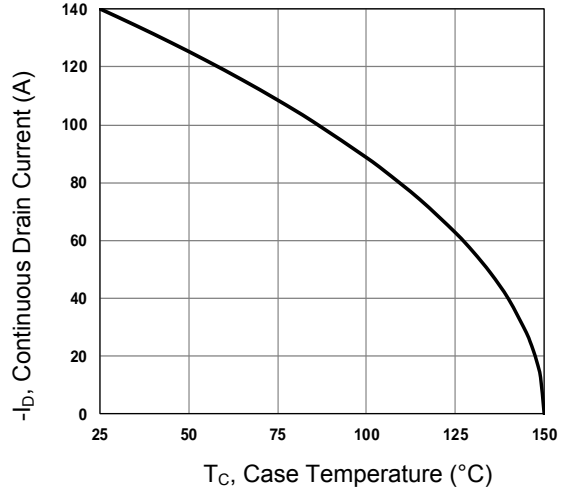


Figure 2. Continuous Drain Current vs. Tc

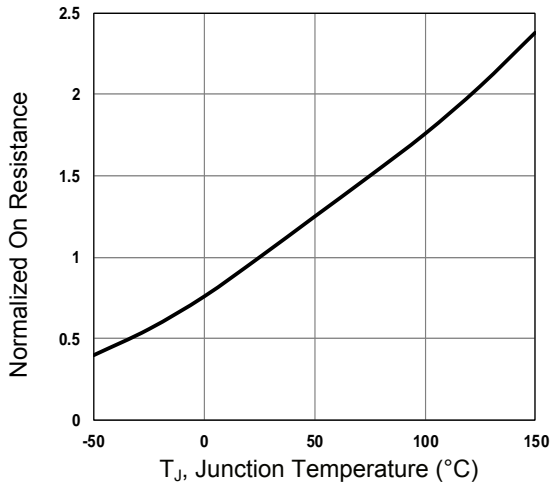


Figure 3. Normalized $R_{DS(on)}$ vs. T_J

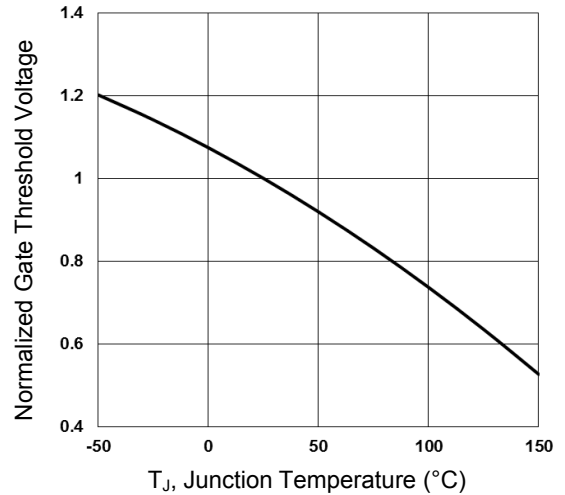


Figure 4. Normalized V_{th} vs. T_J

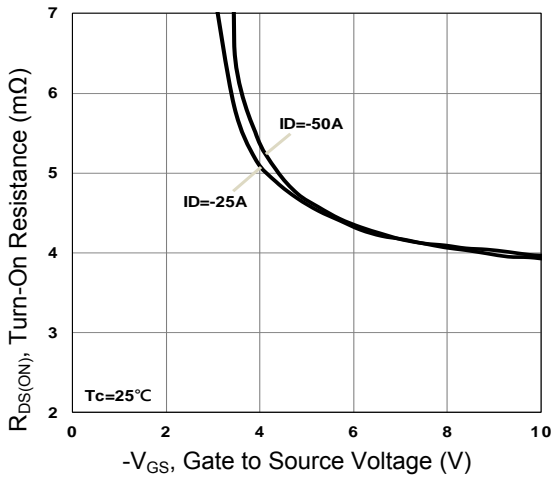


Figure 5. Turn-On Resistance vs. V_{GS}

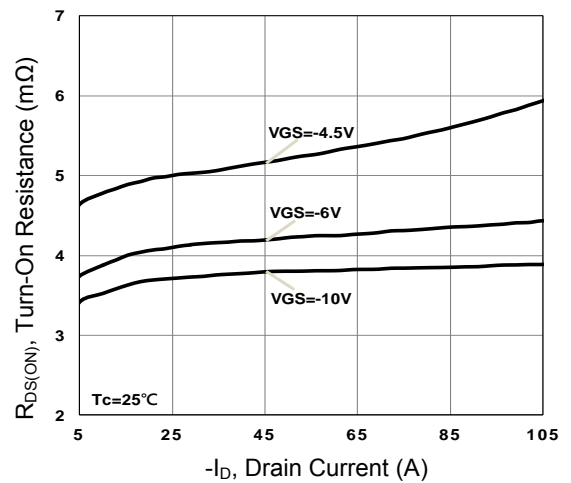


Figure 6. Turn-On Resistance vs. I_D

Typical Electrical and Thermal Characteristic Curves

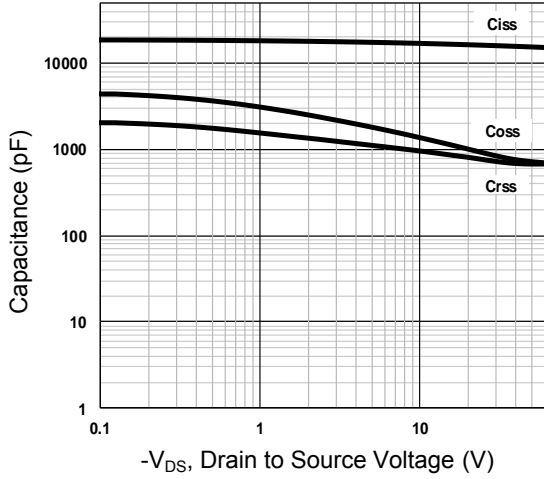


Figure 7. Capacitance Characteristics

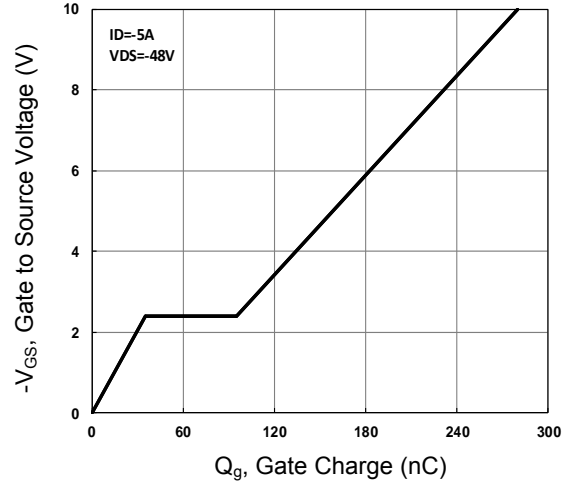


Figure 8. Gate Charge Characteristics

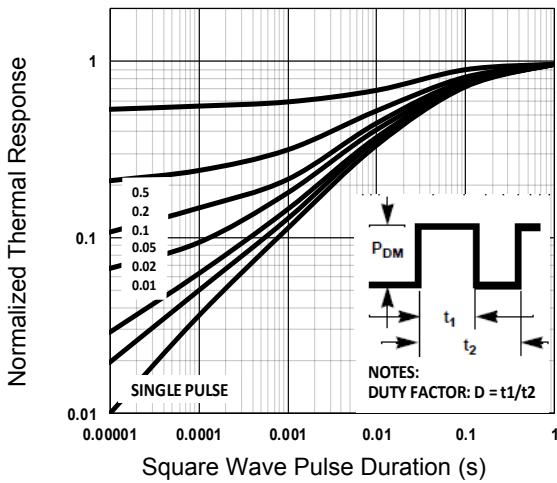


Figure 9. Normalized Transient Impedance

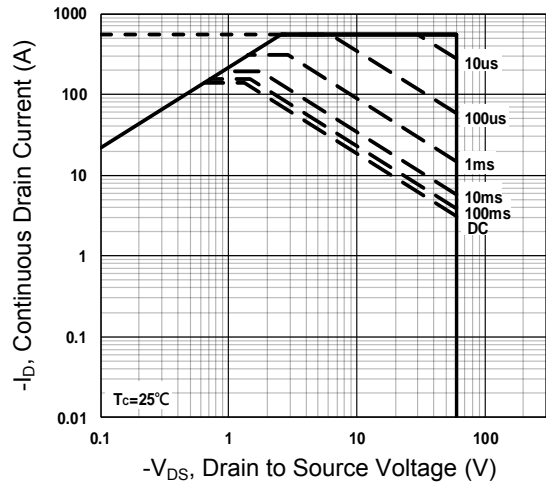


Figure 10. Maximum Safe Operation Area

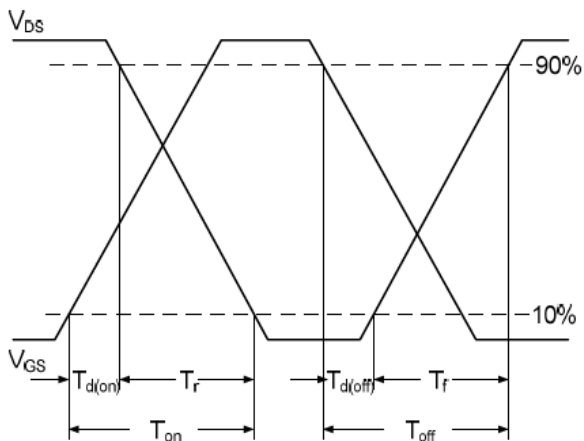


Figure 11. Switching Time Waveform

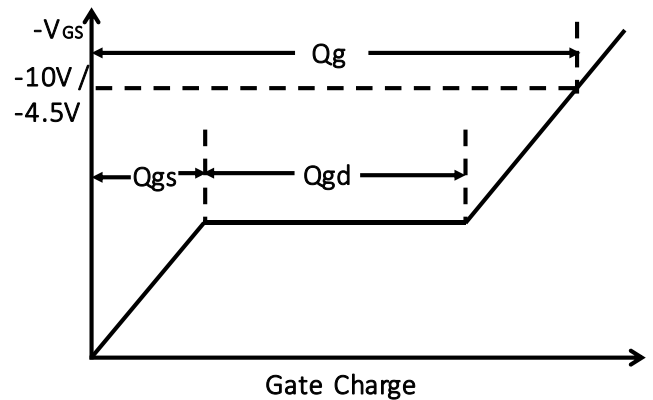
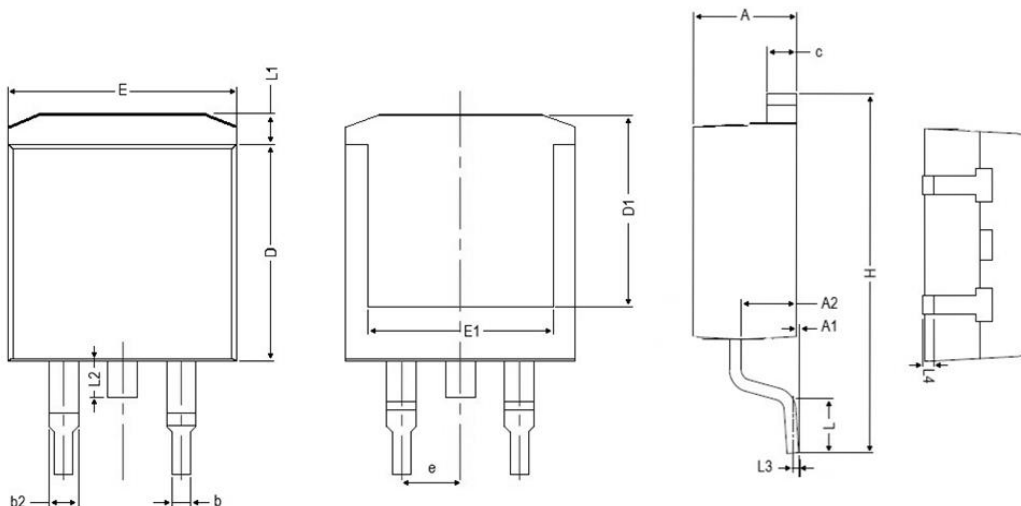


Figure 12. Gate Charge Waveform

Package Outline Dimensions TO-263 (D²PAK)



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min	Max	Min	Max
A	4.200	4.850	0.165	0.191
A1	0.000	0.300	0.000	0.012
A2	2.200	2.900	0.087	0.114
b	0.700	0.950	0.028	0.037
b2	1.000	1.700	0.039	0.067
c	1.150	1.450	0.045	0.057
D	8.350	9.500	0.329	0.374
D1	6.400	9.150	0.252	0.360
E	9.600	10.500	0.378	0.413
E1	6.850	8.900	0.270	0.350
e	2.540 BSC		0.100 BSC	
H	14.600	15.900	0.575	0.626
L	1.700	2.800	0.067	0.110
L1	1.050	1.700	0.041	0.067
L2	1.300	2.100	0.051	0.083
L3	0.250 BSC		0.010 BSC	
L4	0.200	0.750	0.008	0.03

Order Information

Device	Package	Marking	Carrier	Quantity
GSFT06130	TO-263 (D ² PAK)	DH6001	Tape & Reel	800pcs / Reel

For more information, please contact us at: inquiry@goodarksemi.com